



TOP SECRET

Fig 2

【図2】

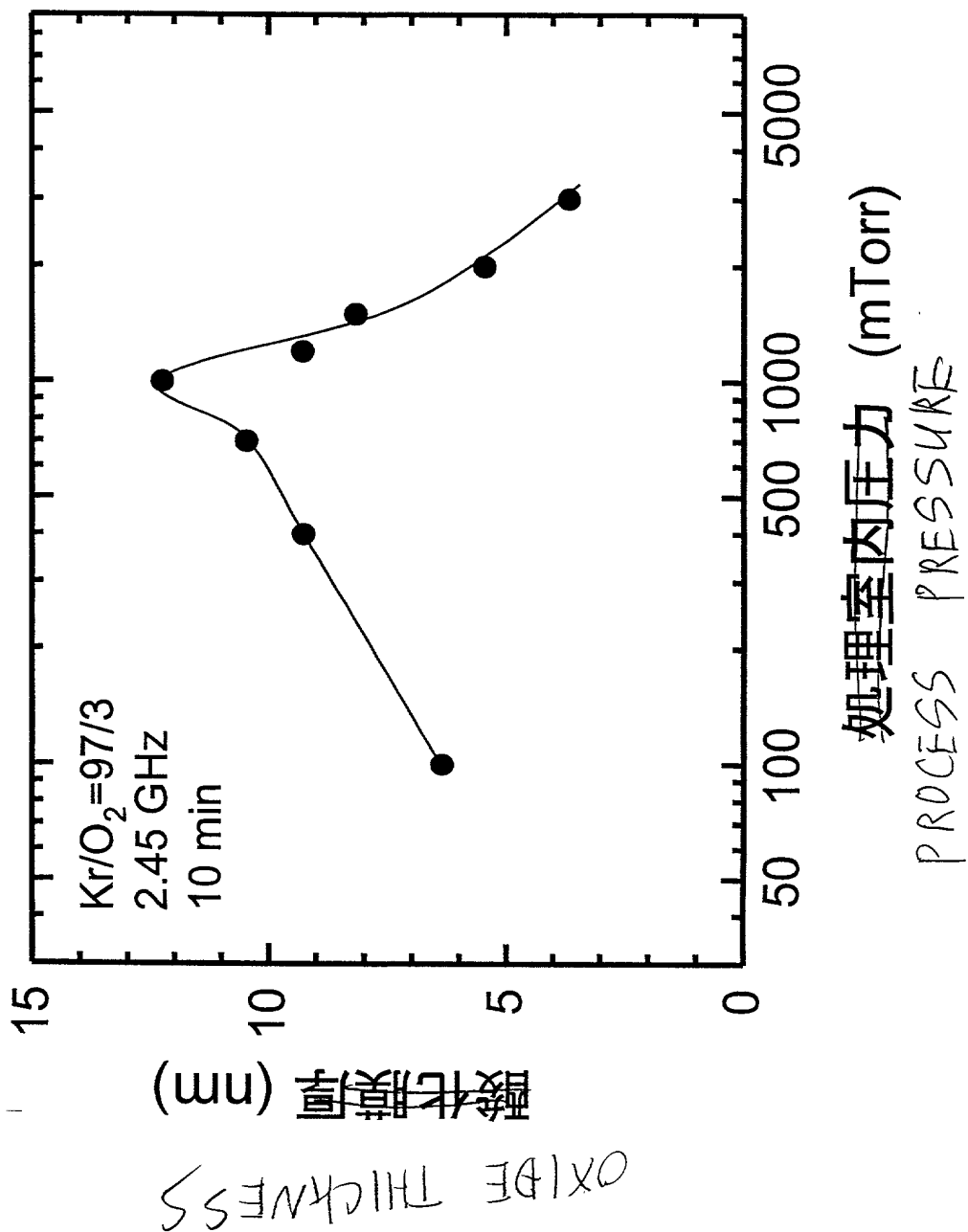
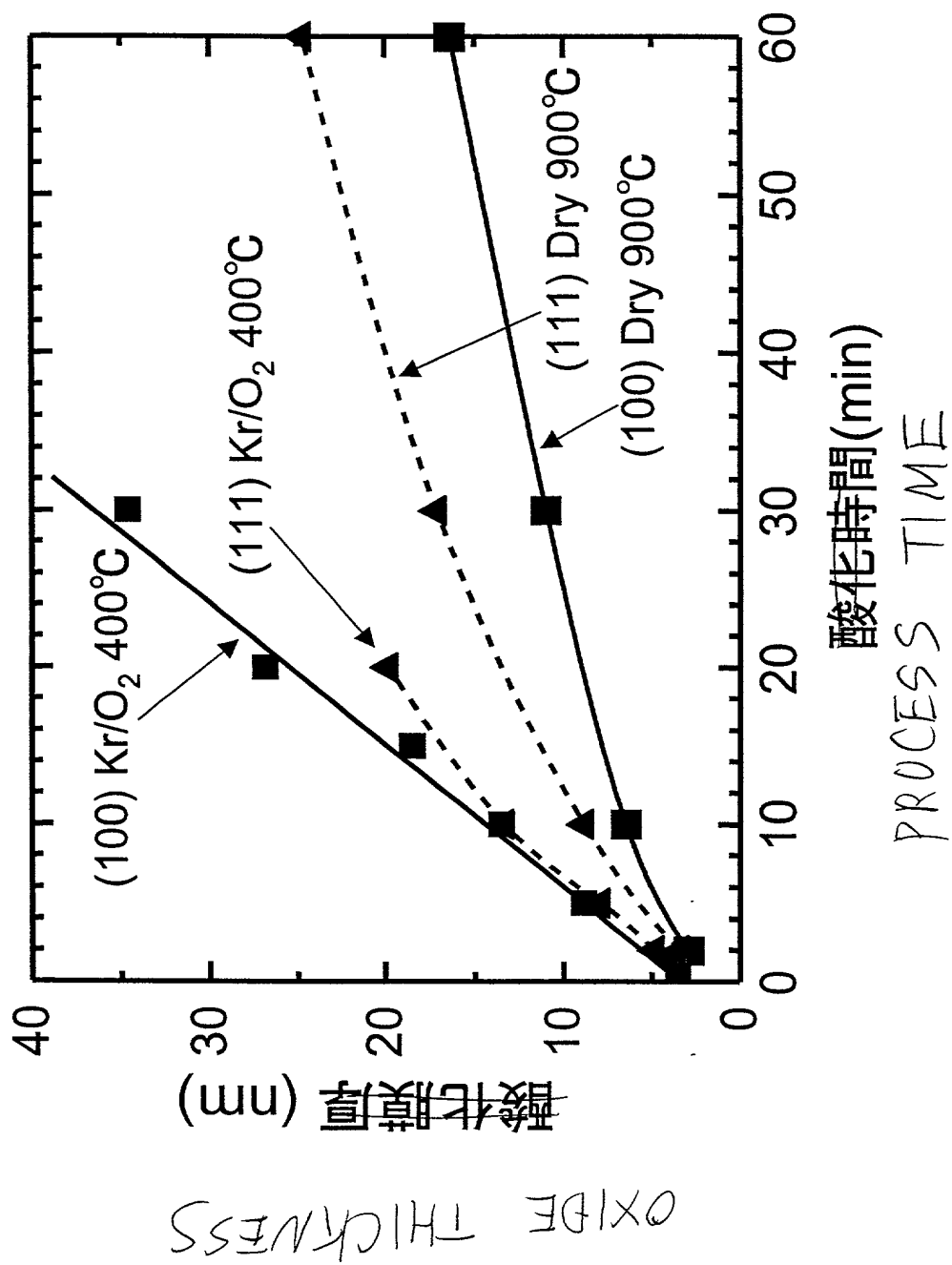


FIG 3

【図3】



TOE HLG

【図4】

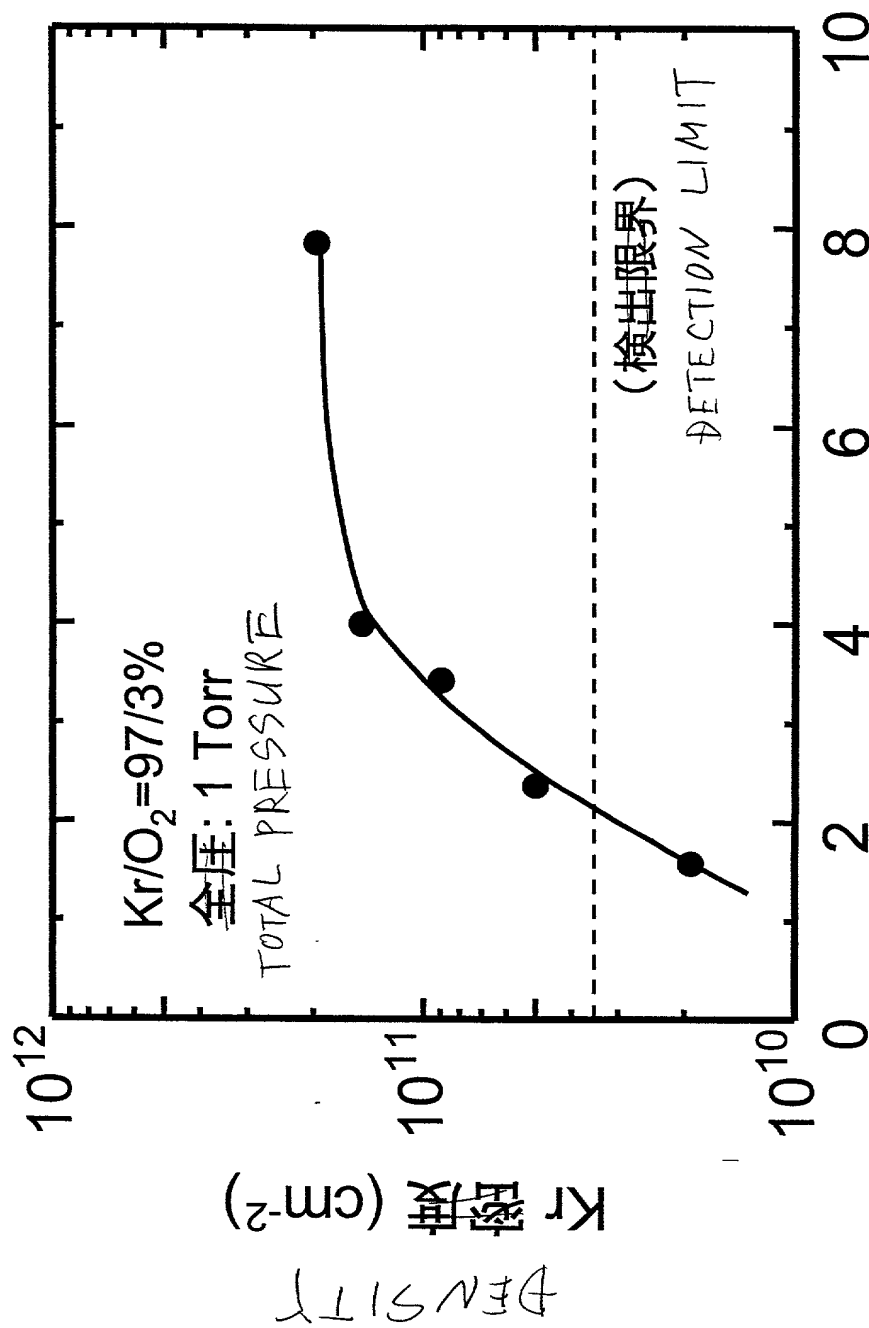


FIG 5

【図5】

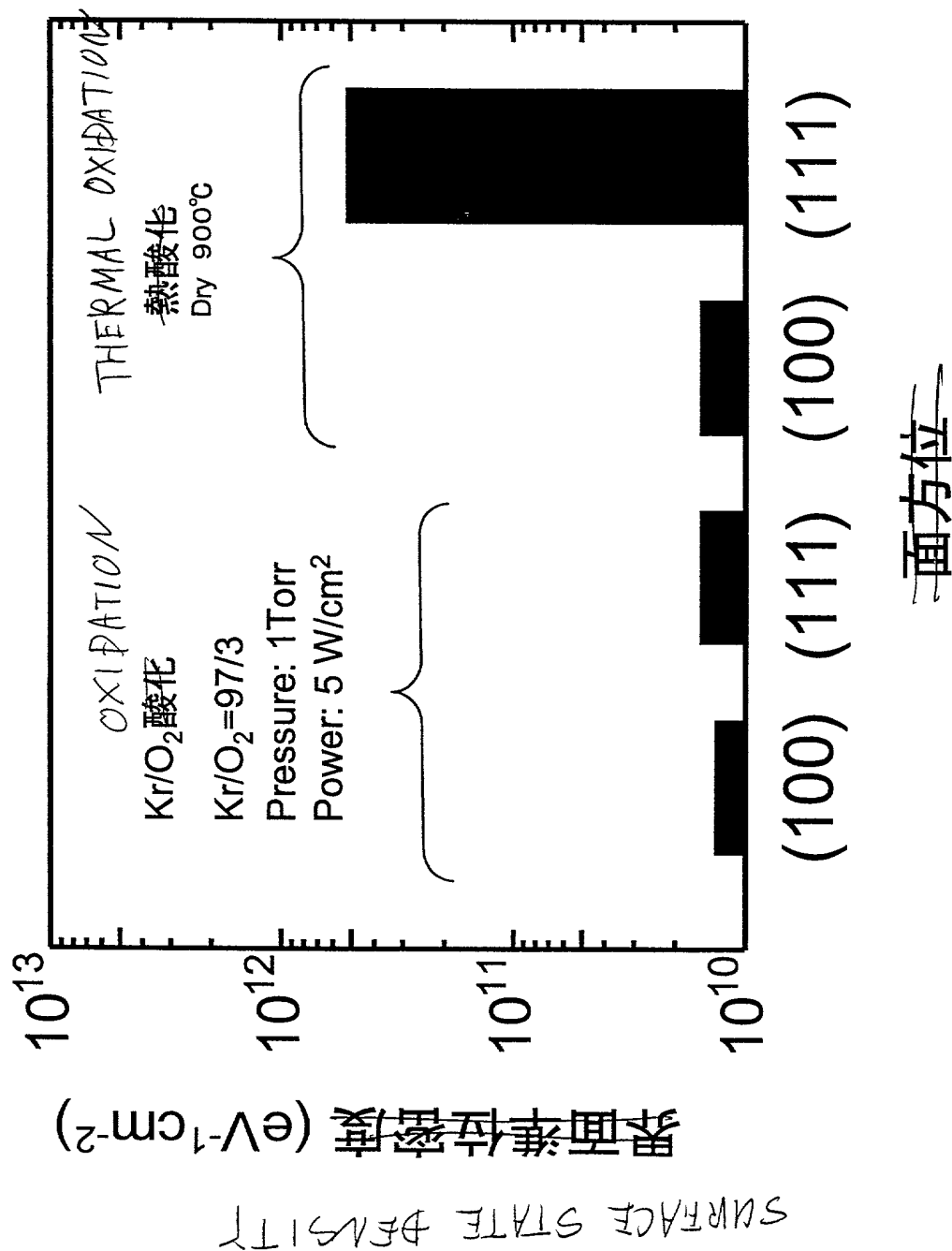
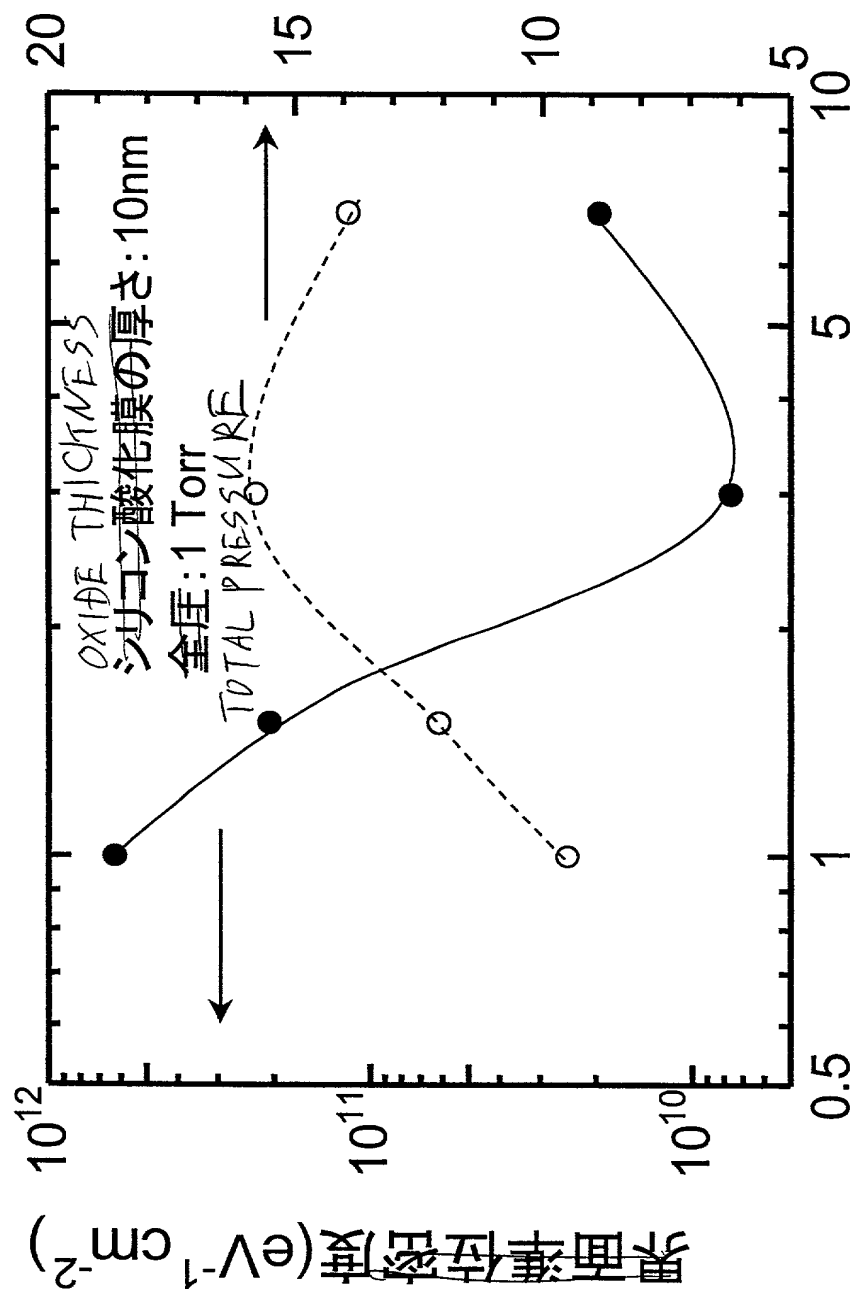


FIG 6

【図6】 AVERAGE BREAKDOWN VOLTAGE (MV/cm)  
平均絶縁耐圧 (MV/cm)

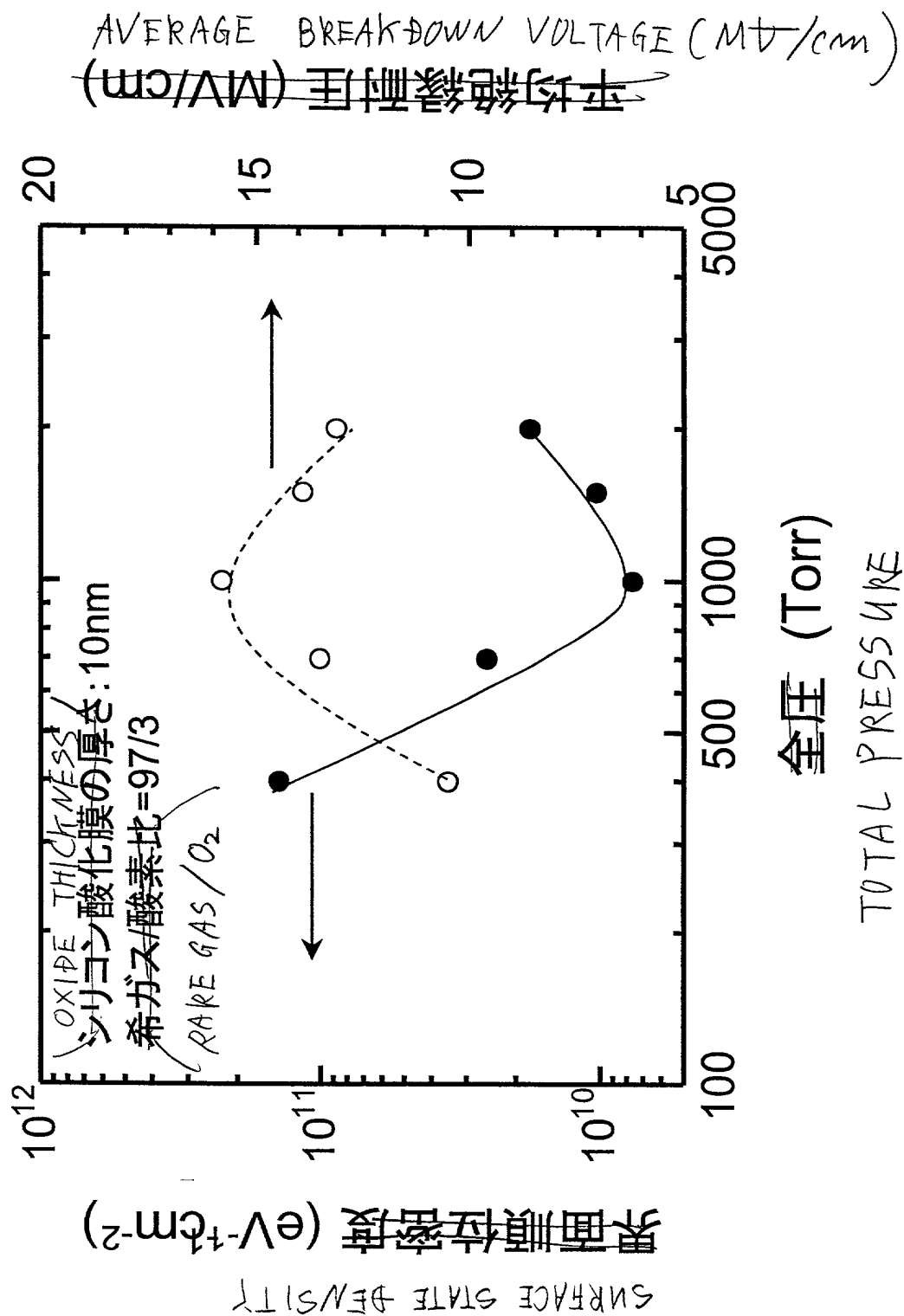


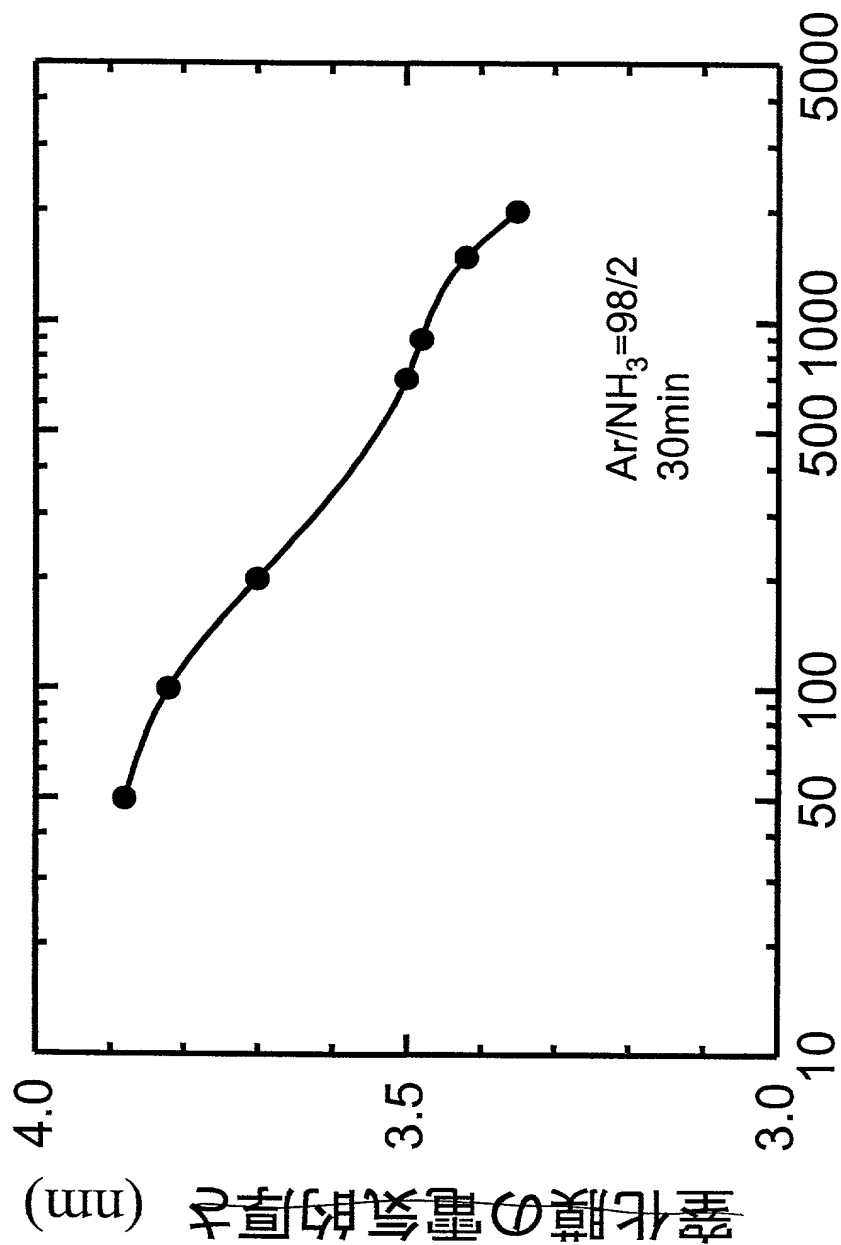
酸素分圧 (%)  
O<sub>2</sub> PARTIAL PRESSURE

SURFACE STATE DENSITY

FIG 7

【図7】





成膜圧力 (mTorr)

PROCESS PRESSURE

窒化膜の電気的厚さ (nm)

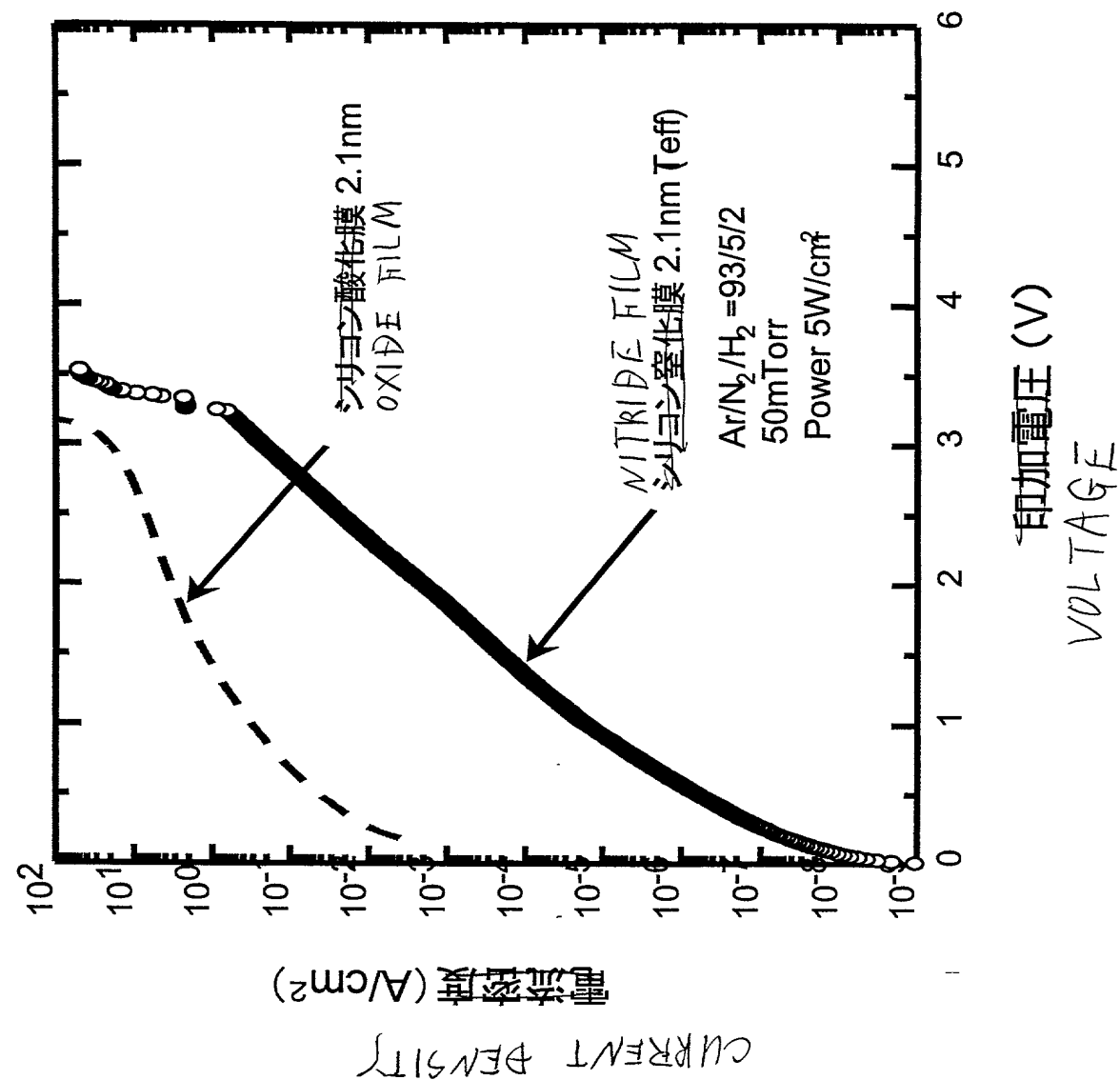
NITRIDE EQUIVALENT THICKNESS

【図8】

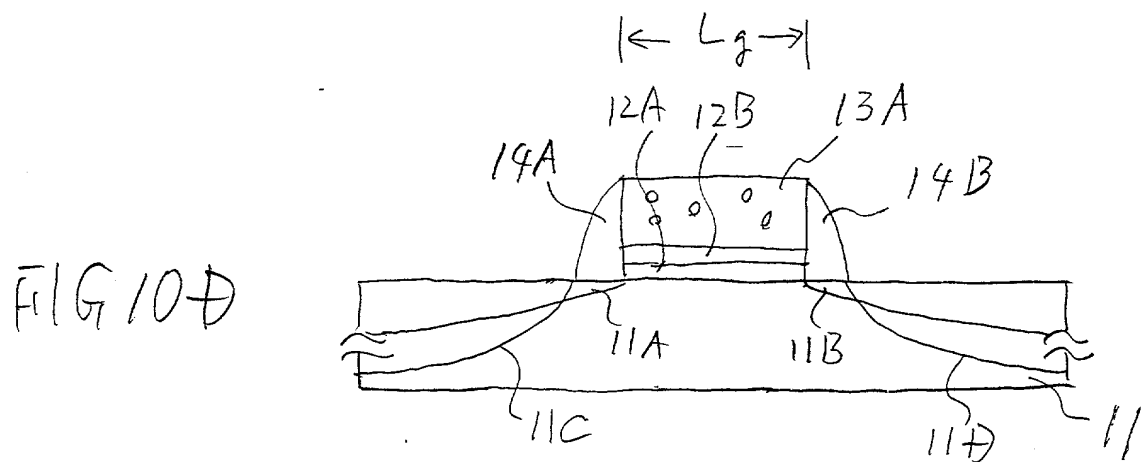
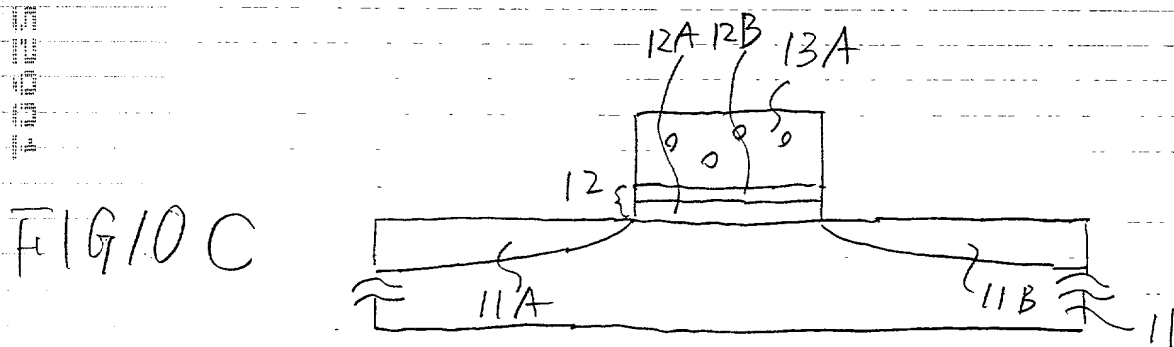
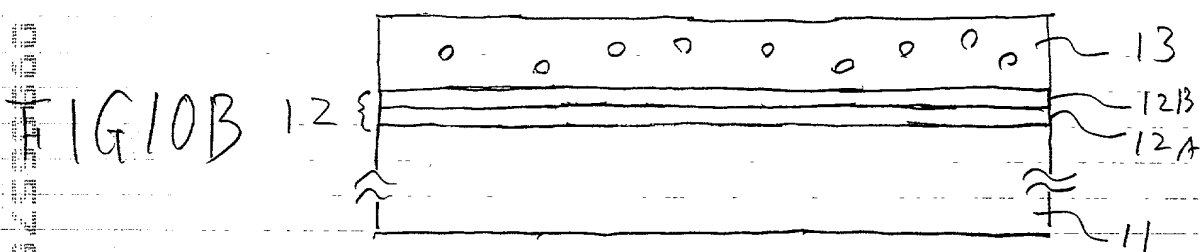
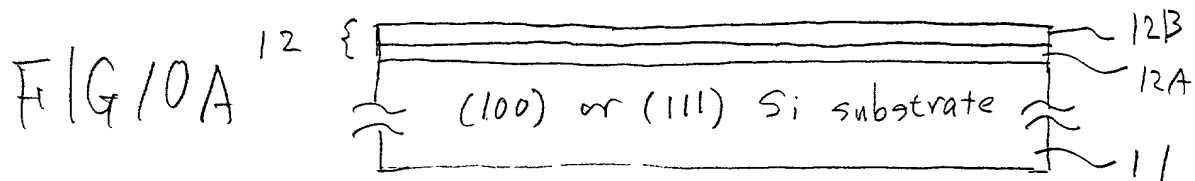
FIG 8



FIG 9



【図9】



【図10】

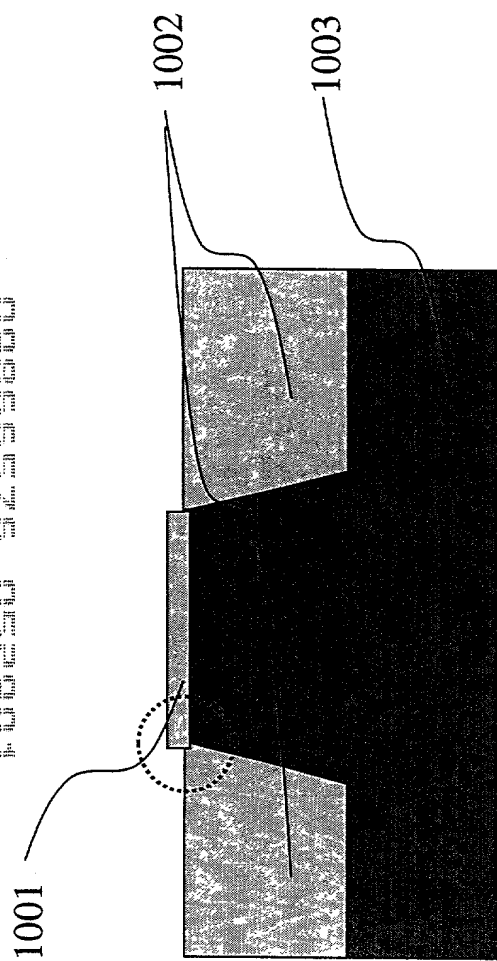
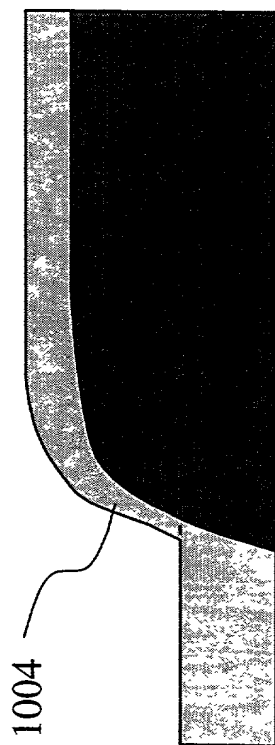
~~FIG 11A(a)~~

FIG 11B ~~(b)~~

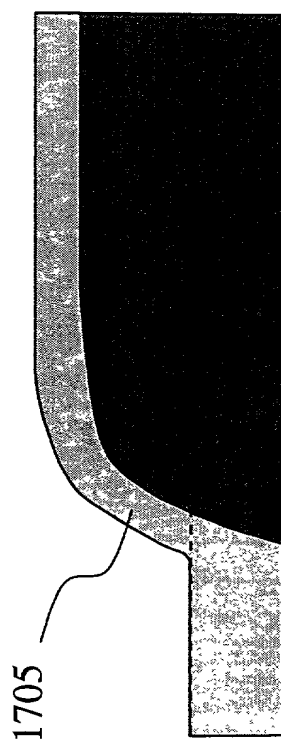


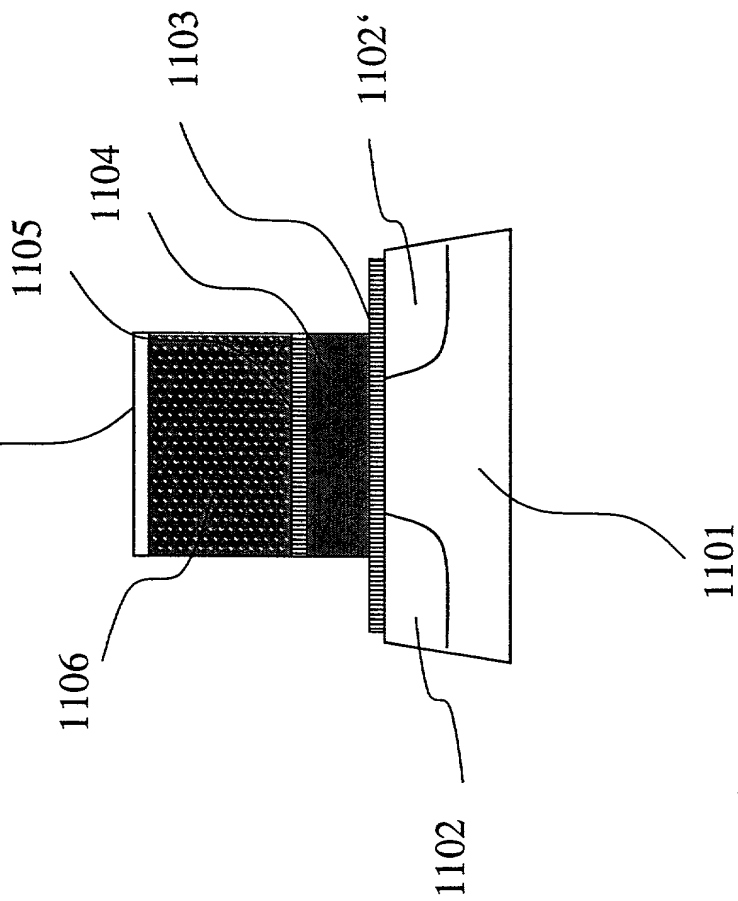
FIG 11C

~~従来例~~ PRIOR ART

本發明 PRESENT INVENTION

FIG 12

1107



【图11】

FIG. 12

【図12】

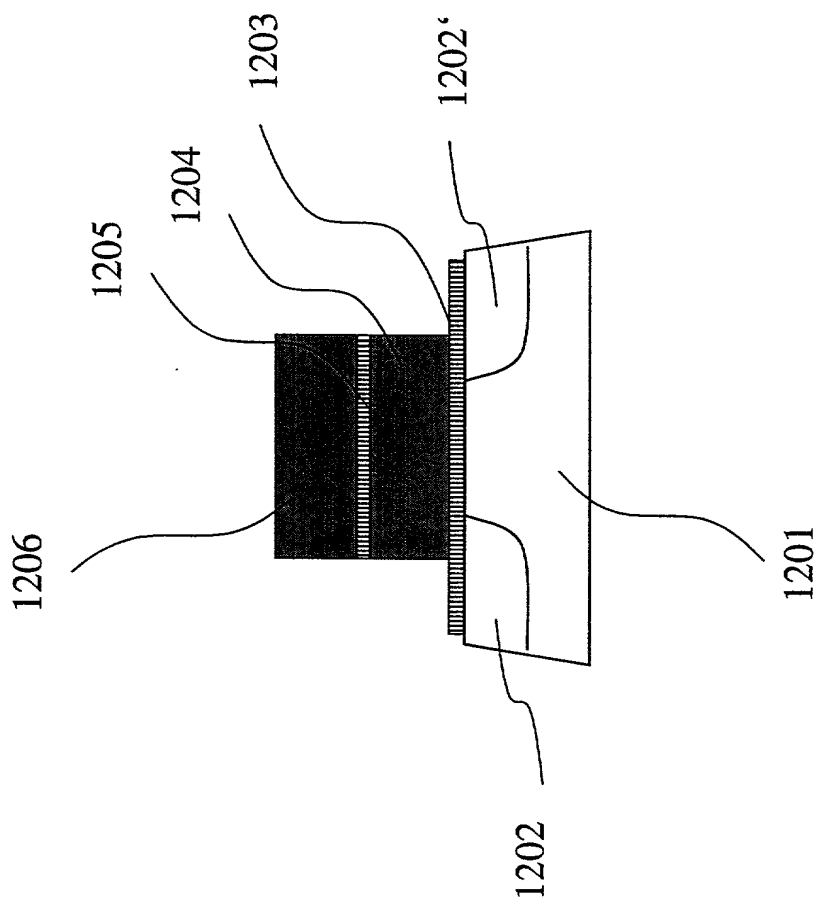
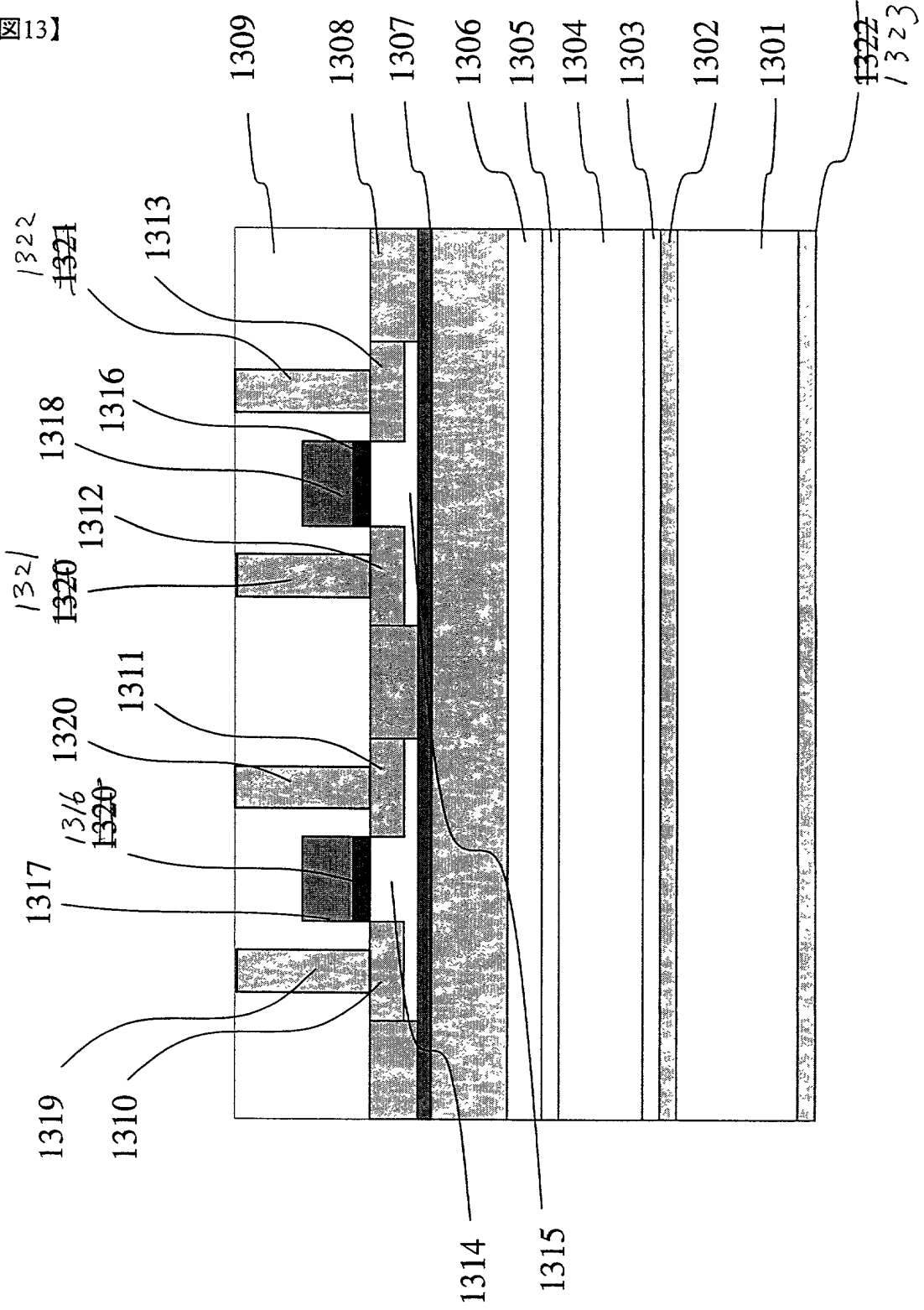


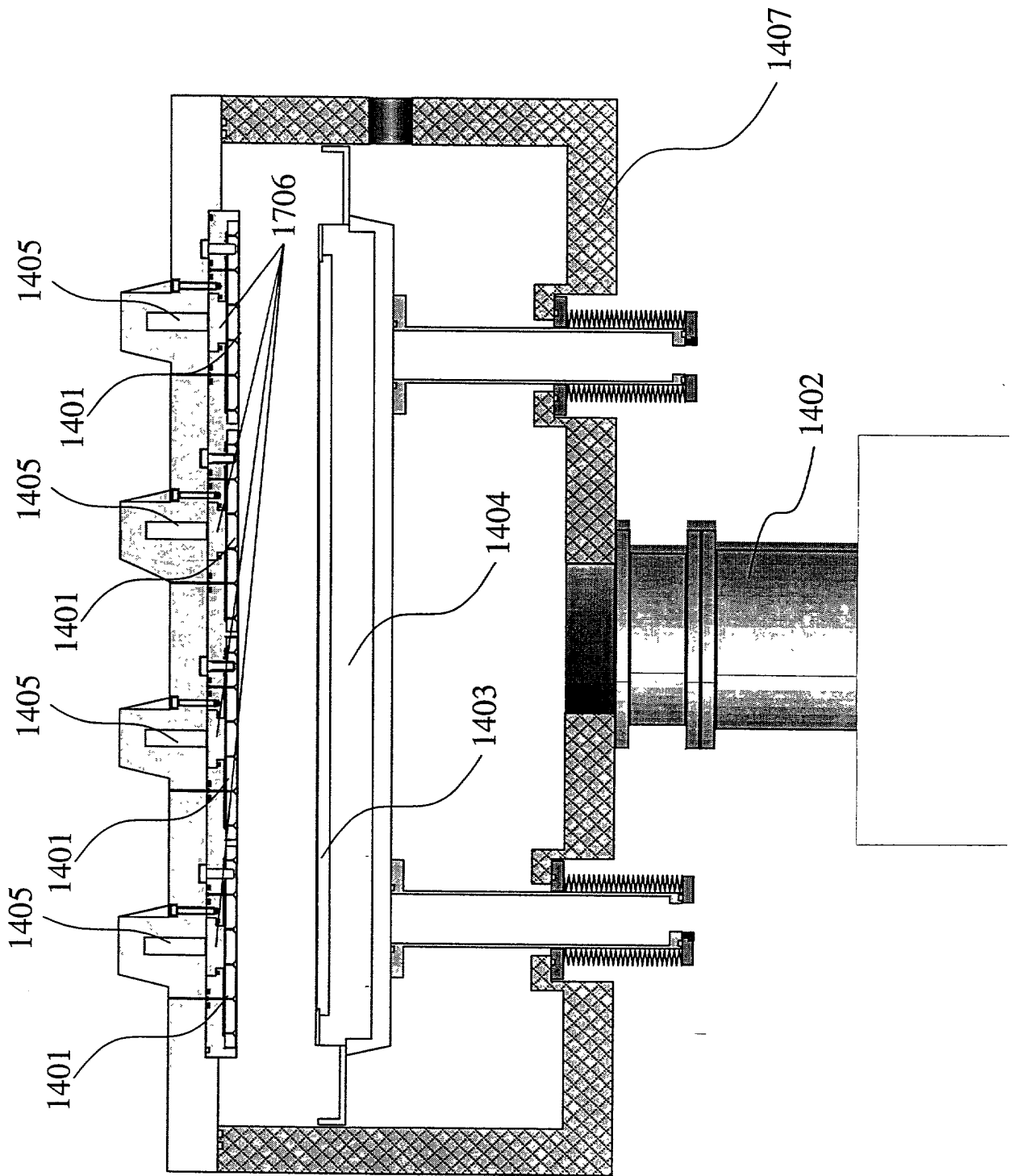
FIG. 14

【図13】



特許庁  
H16.5.5  
55555555

【図14】







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【図16】

